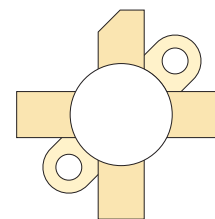


RF POWER VERTICAL MOSFET

The VRF141 is a gold-metallized silicon n-channel RF power transistor designed for broadband commercial and military applications requiring high power and gain without compromising reliability, ruggedness, or inter-modulation distortion.



FEATURES

- Improved Ruggedness $V_{(BR)DSS} = 80\text{ V}$
- 150W with 22dB Typical Gain @ 30MHz, 28V
- 150W with 13dB Typical Gain @ 175MHz, 28V
- Excellent Stability & Low IMD
- Common Source Configuration
- Available in Matched Pairs
- 30:1 Load VSWR Capability at Specified Operating Conditions
- Nitride Passivated
- Refractory Gold Metallization
- High Voltage Replacement for MRF141
- RoHS Compliant

Maximum Ratings

All Ratings: $T_c = 25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	VRF141(MP)	Unit
V_{DSS}	Drain-Source Voltage	80	V
I_D	Continuous Drain Current @ $T_c = 25^\circ\text{C}$	20	A
V_{GS}	Gate-Source Voltage	± 40	V
P_D	Total Device dissipation @ $T_c = 25^\circ\text{C}$	300	W
T_{STG}	Storage Temperature Range	-65 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature	200	

Static Electrical Characteristics

Symbol	Parameter	Min	Typ	Max	Unit
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage ($V_{GS} = 0\text{V}$, $I_D = 100\text{mA}$)	80			V
$V_{DS(ON)}$	On State Drain Voltage ($I_{D(ON)} = 10\text{A}$, $V_{GS} = 10\text{V}$)		0.9	1.0	
I_{DSS}	Zero Gate Voltage Drain Current ($V_{DS} = 60\text{V}$, $V_{GS} = 0\text{V}$)			1.0	mA
I_{GSS}	Gate-Source Leakage Current ($V_{DS} = \pm 20\text{V}$, $V_{GS} = 0\text{V}$)			1.0	μA
g_{fs}	Forward Transconductance ($V_{DS} = 10\text{V}$, $I_D = 5\text{A}$)	5.0			mhos
$V_{GS(TH)}$	Gate Threshold Voltage ($V_{DS} = 10\text{V}$, $I_D = 100\text{mA}$)	2.9	3.6	4.4	V

Thermal Characteristics

Symbol	Characteristic	Min	Typ	Max	Unit
$R_{\theta JC}$	Junction to Case Thermal Resistance			0.60	$^\circ\text{C/W}$

Dynamic Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input Capacitance	$V_{GS} = 0\text{V}$		400		pF
C_{oss}	Output Capacitance	$V_{DS} = 28\text{V}$		375		
C_{rss}	Reverse Transfer Capacitance	$f = 1\text{MHz}$		50		



CAUTION: These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

Functional Characteristics

VRF141(MP)

Symbol	Parameter	Min	Typ	Max	Unit
G _{PS}	f ₁ = 30MHz, f ₂ = 30.001MHz, V _{DD} = 28V, I _{DQ} = 250mA, P _{out} = 150W _{PEP}	16	20		dB
G _{PS}	f ₁ = 175MHz, V _{DD} = 28V, I _{DQ} = 250mA, P _{out} = 150W		13		
η	f ₁ = 30MHz, f ₂ = 30.001MHz ,V _{DD} = 28V, I _{DQ} = 250mA, P _{out} = 150W _{PEP}	40	45		%
IMD _(d3)	f ₁ = 30MHz, f ₂ = 30.001MHz, V _{DD} = 28V, I _{DQ} = 250mA, P _{out} = 150W _{PEP} ¹		-30	-28	dB
IMD _(d11)	f ₁ = 30MHz, f ₂ = 30.001MHz, V _{DD} = 28V, I _{DQ} = 250mA, P _{out} = 150W _{PEP}		-60		
ψ	f ₁ = 30MHz, f ₂ = 30.001MHz, V _{DD} = 28V, I _{DQ} = 250mA, P _{out} = 150W _{PEP} 30:1 VSWR - All Phase Angles	No Degradation in Output Power			

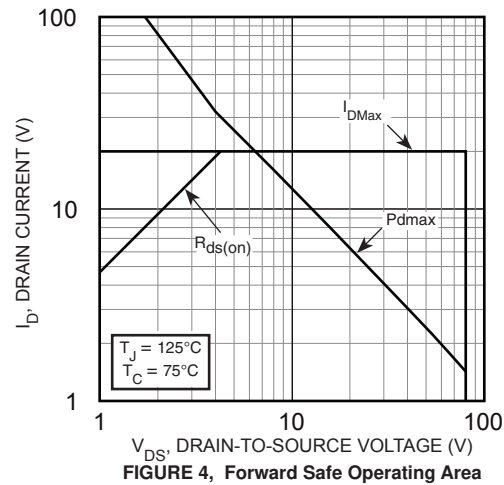
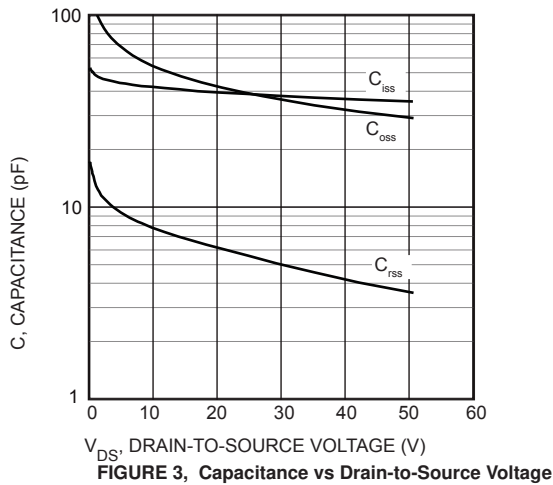
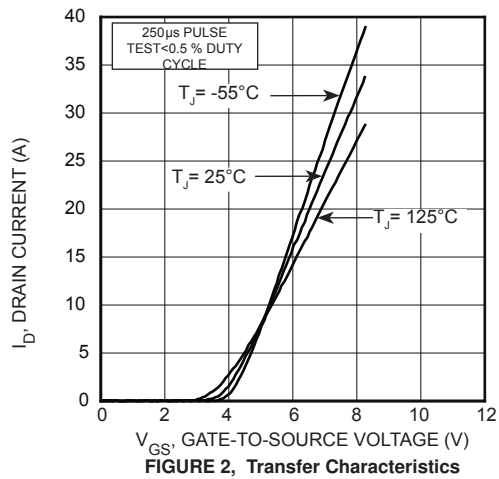
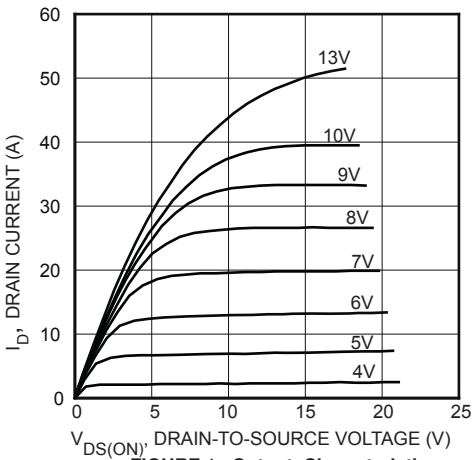
Class A Characteristics

Symbol	Test Conditions	Min	Typ	Max	Unit
G_{PS}	$f_1 = 30\text{MHz}, f_2 = 30.001\text{MHz}, V_{DD} = 28\text{V}, I_{DQ} = 4.0\text{A}, P_{out} = 50\text{W}_{PEP}$		23		dB
$IMD_{(d3)}$	$f_1 = 30\text{MHz}, f_2 = 30.001\text{MHz}, V_{DD} = 28\text{V}, I_{DQ} = 4.0\text{A}, P_{out} = 50\text{W}_{PEP}$		-50		
$IMD_{(d9-d13)}$	$f_1 = 30\text{MHz}, f_2 = 30.001\text{MHz}, V_{DD} = 28\text{V}, I_{DQ} = 4.0\text{A}, P_{out} = 50\text{W}_{PEP}$		-75		

1. To MIL-STD-1311 Version A, test method 2204B, Two Tone, Reference Each Tone

Microsemi reserves the right to change, without notice, the specifications and information contained herein.

Typical Performance Curves



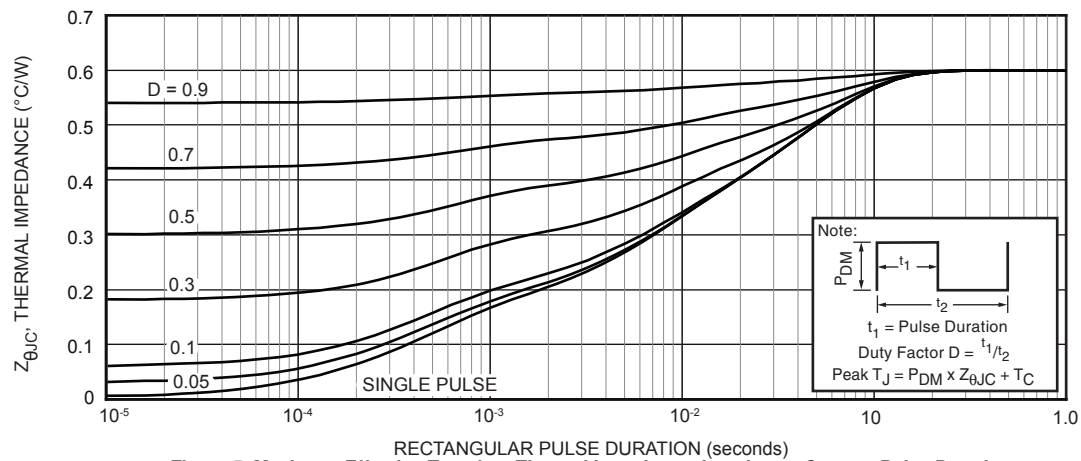
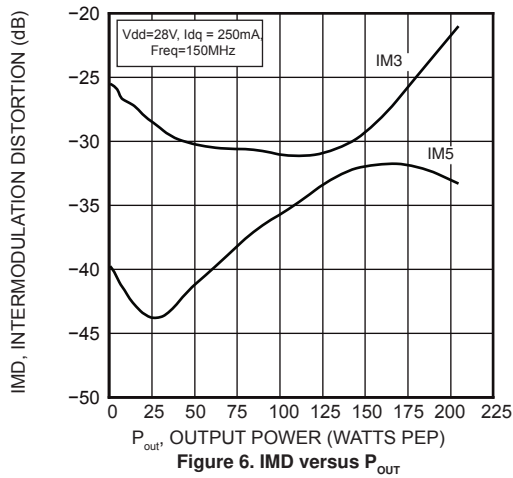
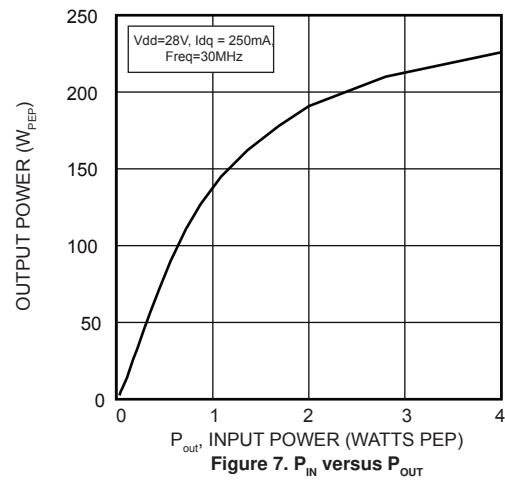
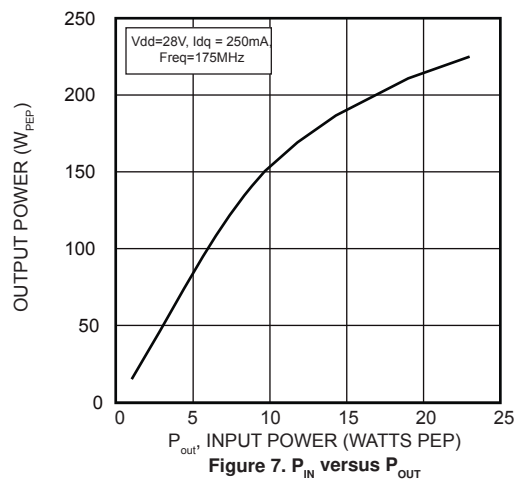
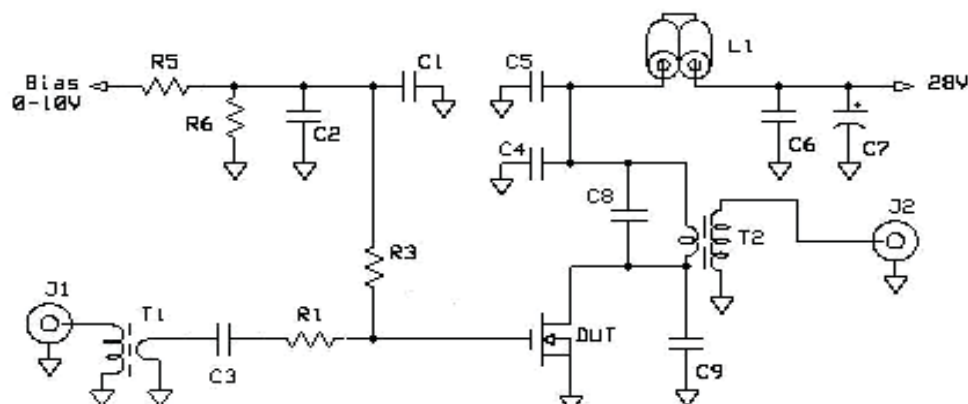


Figure 5. Maximum Effective Transient Thermal Impedance Junction-to-Case vs Pulse Duration

Figure 6. IMD versus P_{OUT} Figure 7. P_{IN} versus P_{OUT} Figure 7. P_{IN} versus P_{OUT}

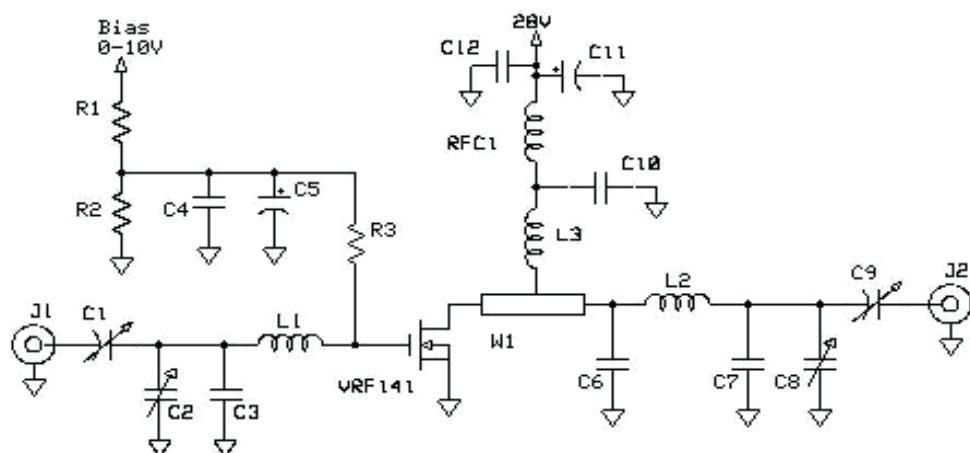
30 MHz test Circuit



C1 - 1 μ F 50V tantalum
 C2-C6 - 0.1 μ F 100V SMT
 C7 - 15 μ F 100V Elect
 C8 - 820 pF ATC 100B
 T1 - 16:1 bead/tube transformer
 T2 = 1:25 broadband bead/tube
 transformer u=125

C9 - 100 pF ATC 100B
 L1 - two ferrite beads on #18
 R1 - 1 ohm 1 W SMT
 R3 - 200 ohm 1/2 Carbon
 R4 - 470 ohm 1W
 R5 R6 - 2200 ohm 1/4W

175 MHz test Circuit



C1, 2, 8, 9 - ARCO 463
 C3 C7 - 25 pF ATC 100B
 C4 C10 C12 - 0.1 μ F 100V SMT
 C5 - 1 μ F 150V tant
 C6 - 270 pF ATC 100B
 C10 - .05 100V 1206 SMT
 C11 - 15 μ F 100V Elect

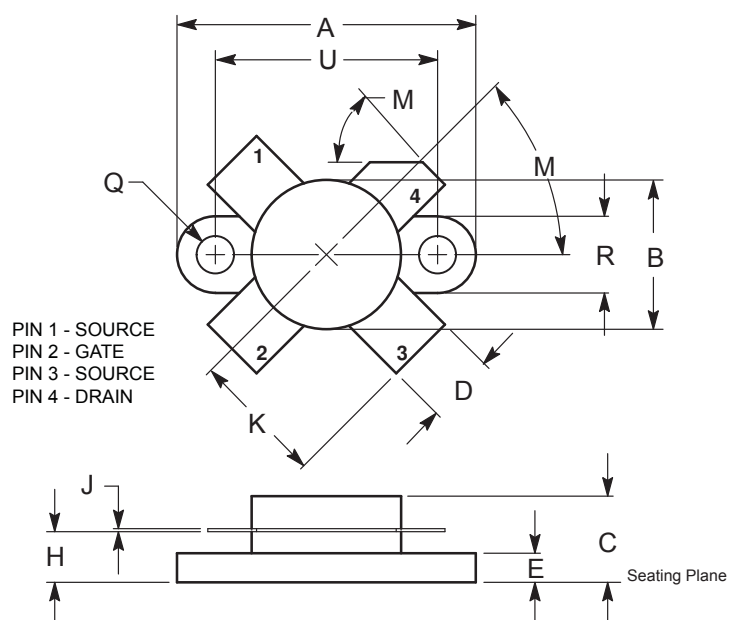
L1 - 3/4" #18 ga into Hairpin
 W1 - printed line 0.23"W x 0.7" L
 L2 - 2t #16 ga .25" dia x .25" ~ 35nH
 L3 - 2 turns #16 ga 5/16" ID tight. ~ 50nH
 R1 R2 - 2.2k ohm 1/4W
 R3 - 150 ohm 1/4W
 RFC1 Fair-Rite 2961666631 (VK200-4B)

Adding MP at the end of P/N specifies a matched pair where $V_{GS(TH)}$ is matched between the two parts. V_{TH} values are marked on the devices per the following table.

Code	Vth Range	Code 2	Vth Range
A	2.900 - 2.975	M	3.650 - 3.725
B	2.975 - 3.050	N	3.725 - 3.800
C	3.050 - 3.125	P	3.800 - 3.875
D	3.125 - 3.200	R	3.875 - 3.950
E	3.200 - 3.275	S	3.950 - 4.025
F	3.275 - 3.350	T	4.025 - 4.100
G	3.350 - 3.425	W	4.100 - 4.175
H	3.425 - 3.500	X	4.175 - 4.250
J	3.500 - 3.575	Y	4.250 - 4.325
K	3.575 - 3.650	Z	4.325 - 4.400

V_{TH} values are based on Microsemi measurements at datasheet conditions with an accuracy of 1.0%.

M174 Package Outline .5" SOE
All Dimensions to be ± 0.005 "



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.096	0.990	24.39	25.14
B	0.465	0.510	11.82	12.95
C	0.229	0.275	5.82	6.98
D	0.216	0.235	5.49	5.96
E	0.084	0.110	2.14	2.79
H	0.144	0.178	3.66	4.52
J	0.003	0.007	0.08	0.17
K	0.435		11.0	
M	45° NOM		45° NOM	
Q	0.115	0.130	2.93	3.30
R	0.246	0.255	6.25	6.47
U	0.720	0.730	18.29	18.54